



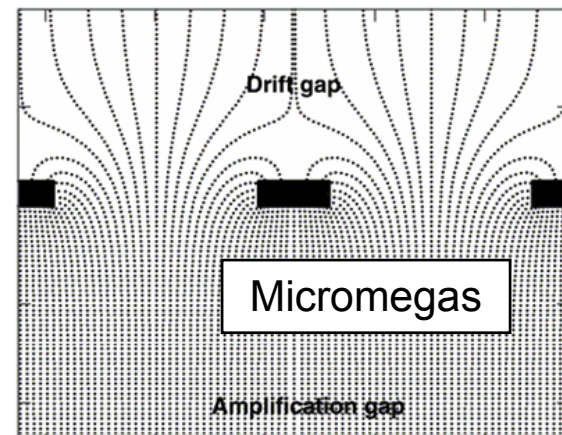
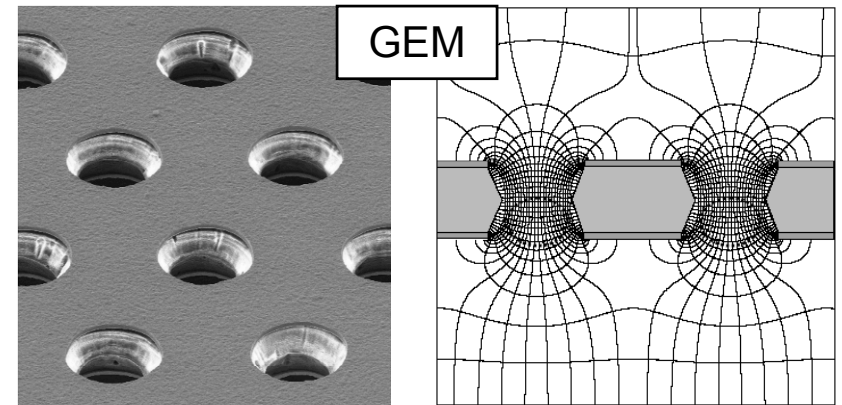
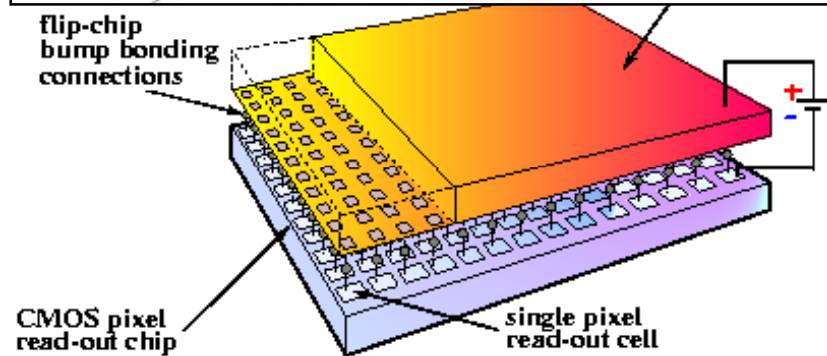
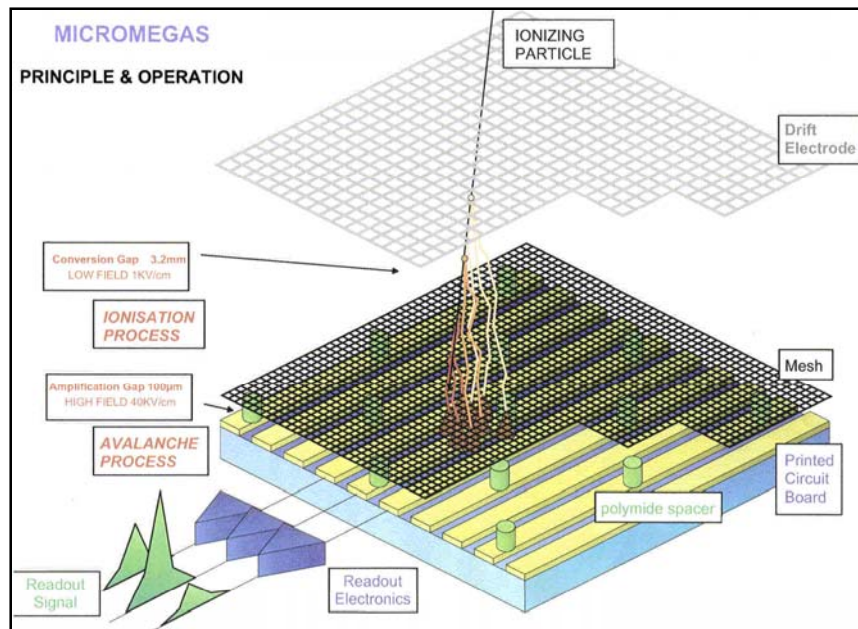
Update on Silicon Pixel Readout for a TPC at NIKHEF

TILC08 - Sendai
4 March 2008

Jan Timmermans
NIKHEF

Micro Patterned Gaseous Detectors

- High field created by Gas Gain Grids
- Most popular: GEM & Micromegas

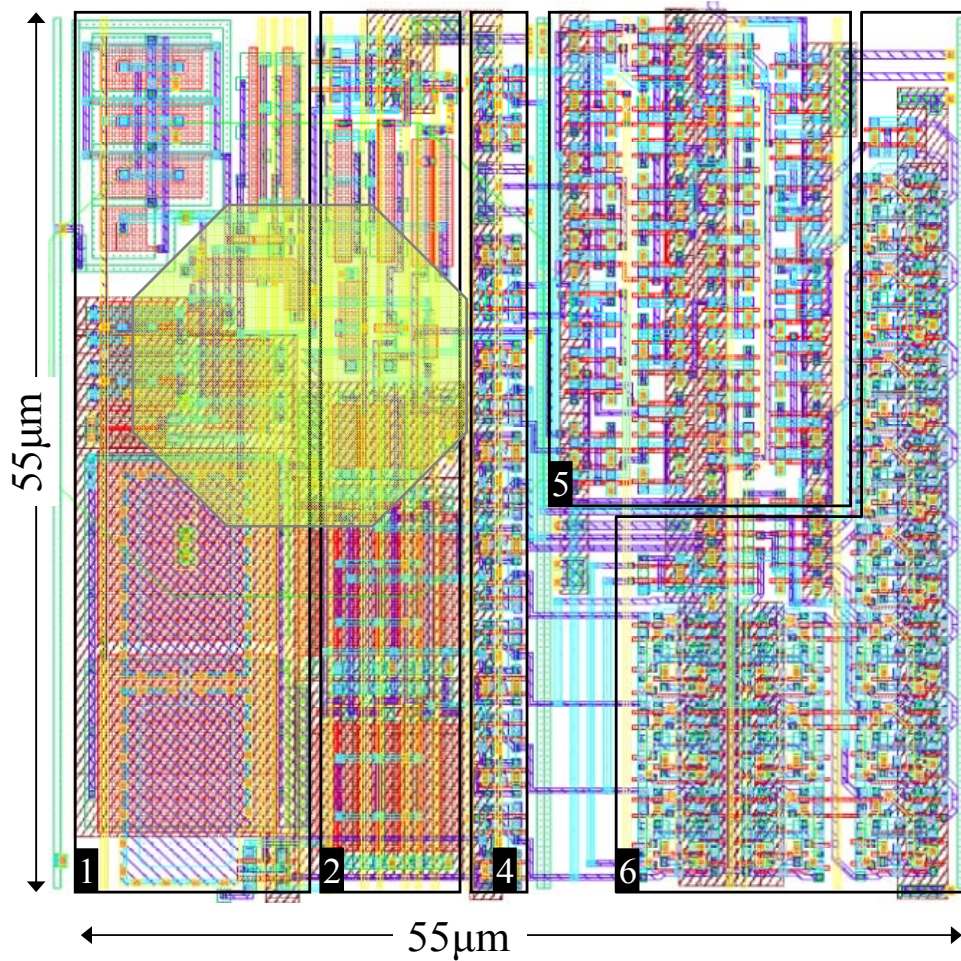


Use 'naked' CMOS pixel readout chip as anode



Timepix pixel

CERN



Timepix chip:

- 256x256 pixels
- pixel: $55 \times 55 \mu\text{m}^2$
- active surface: $14 \times 14 \text{ mm}^2$

Timepix chip (1st version) produced Sept. 2006

Available for use in detectors since Nov. 2006

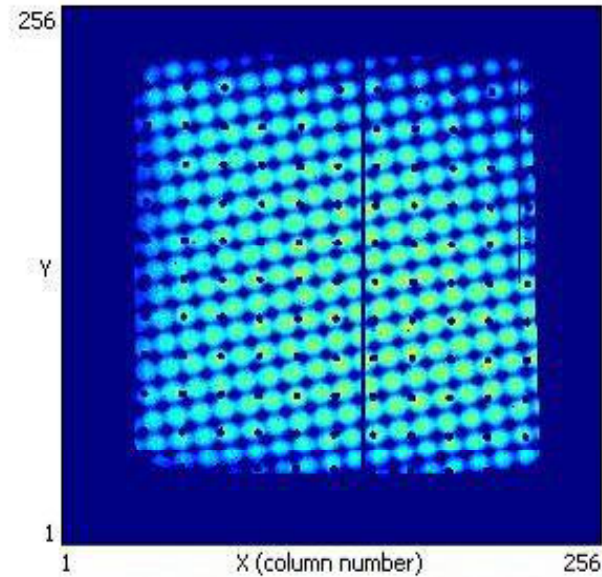
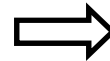
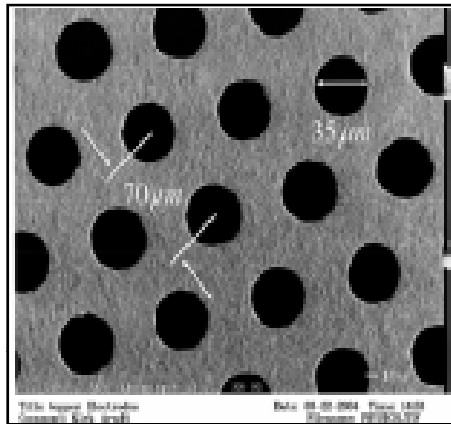
Timepix in gaseous detectors

- With Micromegas grid or GEM stacks
- Wafer postprocessing:
 - Integrated grid (Ingrid)
 - Enlarged pixels (with GEMs @ Freiburg)
- Discharge protection:

high-resistive ($\sim 10^{11}$) $\Omega\cdot\text{cm}$ amorphous Si layer (20 μm thick) on top of CMOS chip
(later maybe also high-resistive grid)

Full post-processing of a TimePix

· Timepix chip + Micromegas mesh:

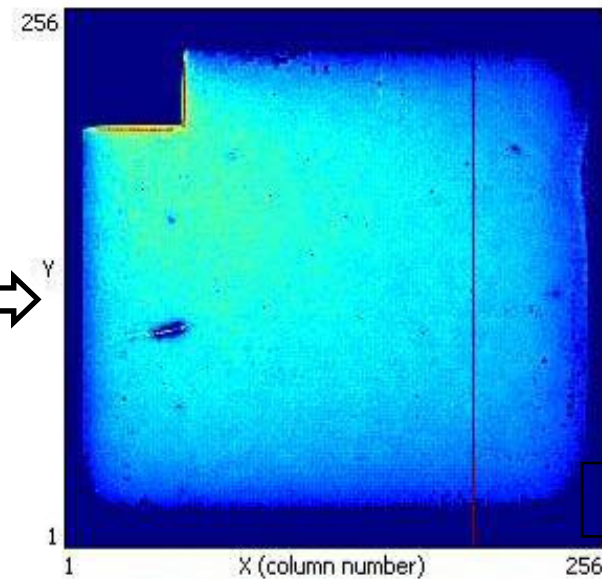
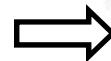
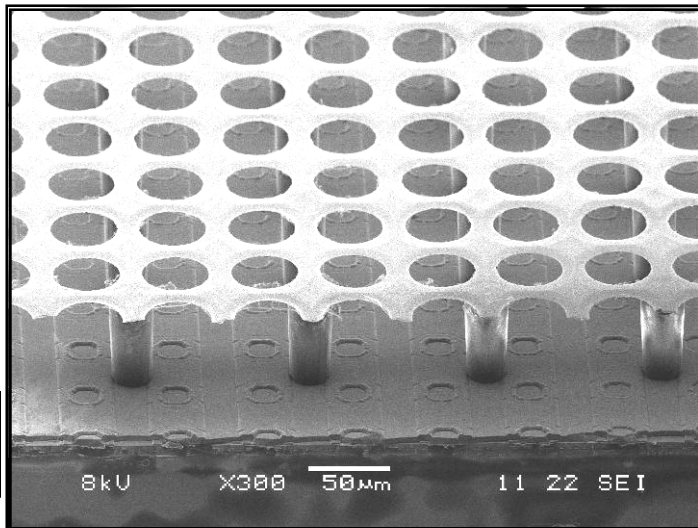


Moiré effects
+ pillars

· Timepix chip + SiProt + Ingrid:

MESA+

IMT
Neuchatel



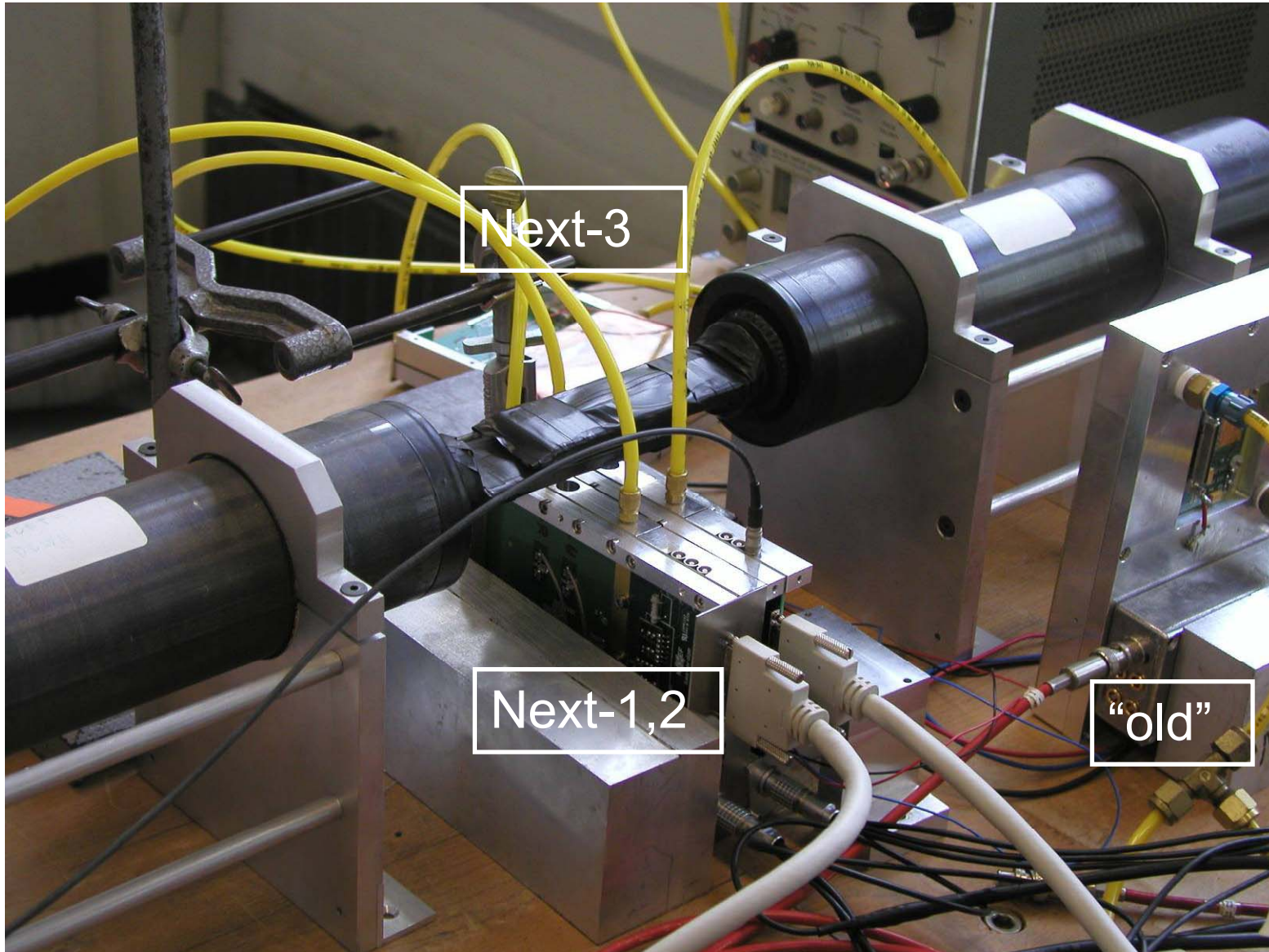
“Uniform”

“counting” mode

“lifetime” of Medipix2/Timepix chips

- “naked” Medipix chips:
up to few hours; sometimes very short!
(both in He and in Ar mixtures)
- With 4 μm amorphous Si:
 - in He/isobutane (80/20): > 3 months
 - In Ar/isobutane (80/20): ~ 1 day!
- With 20 μm protection layer ???

NIKHEF setup (> 22 Aug. 2007)

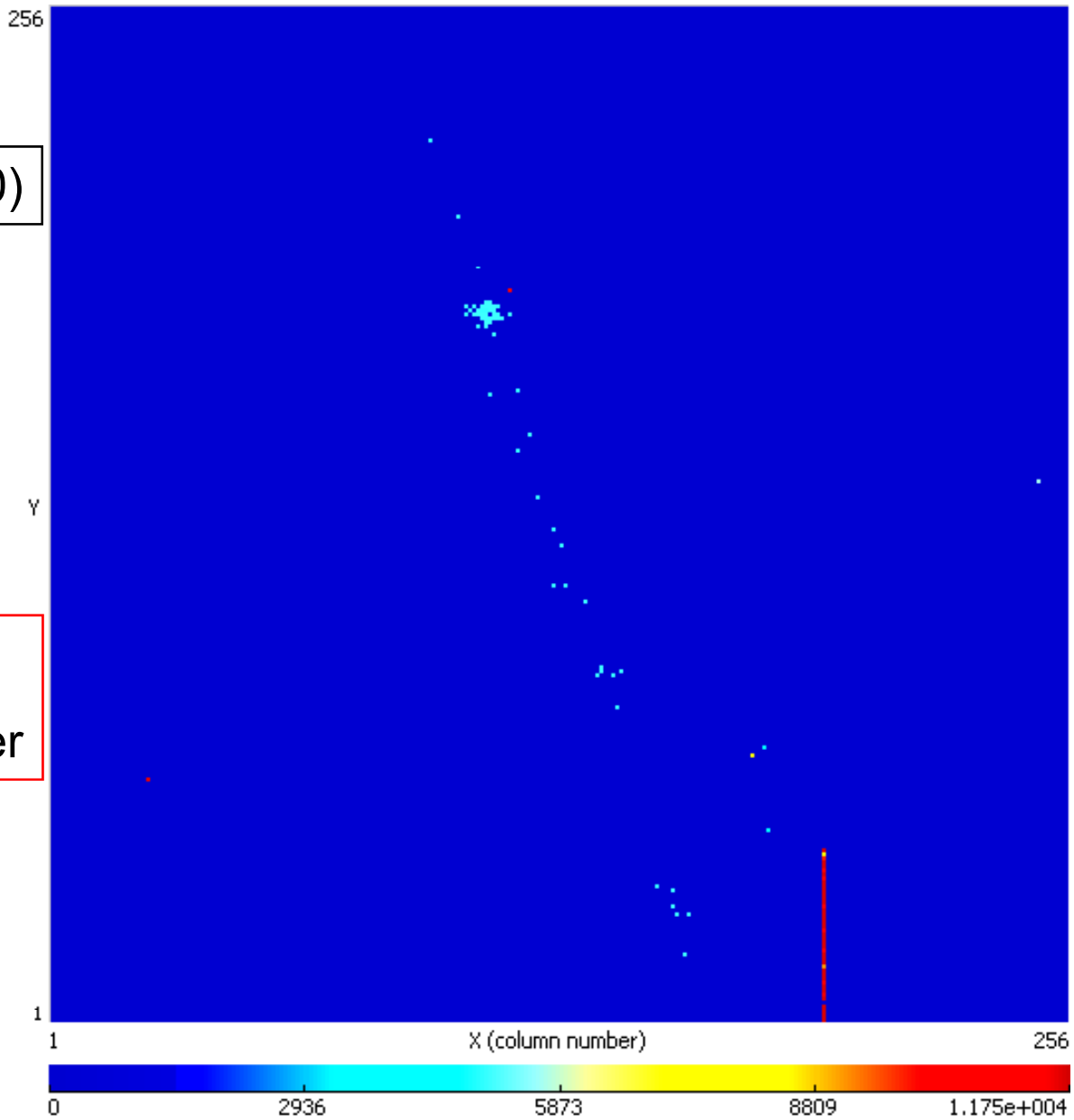


^{90}Sr

He/Iso (80:20)

Time mode

118 μs shutter



Timepix
+
20 μm Siprot
+
Ingrid
in Next-1

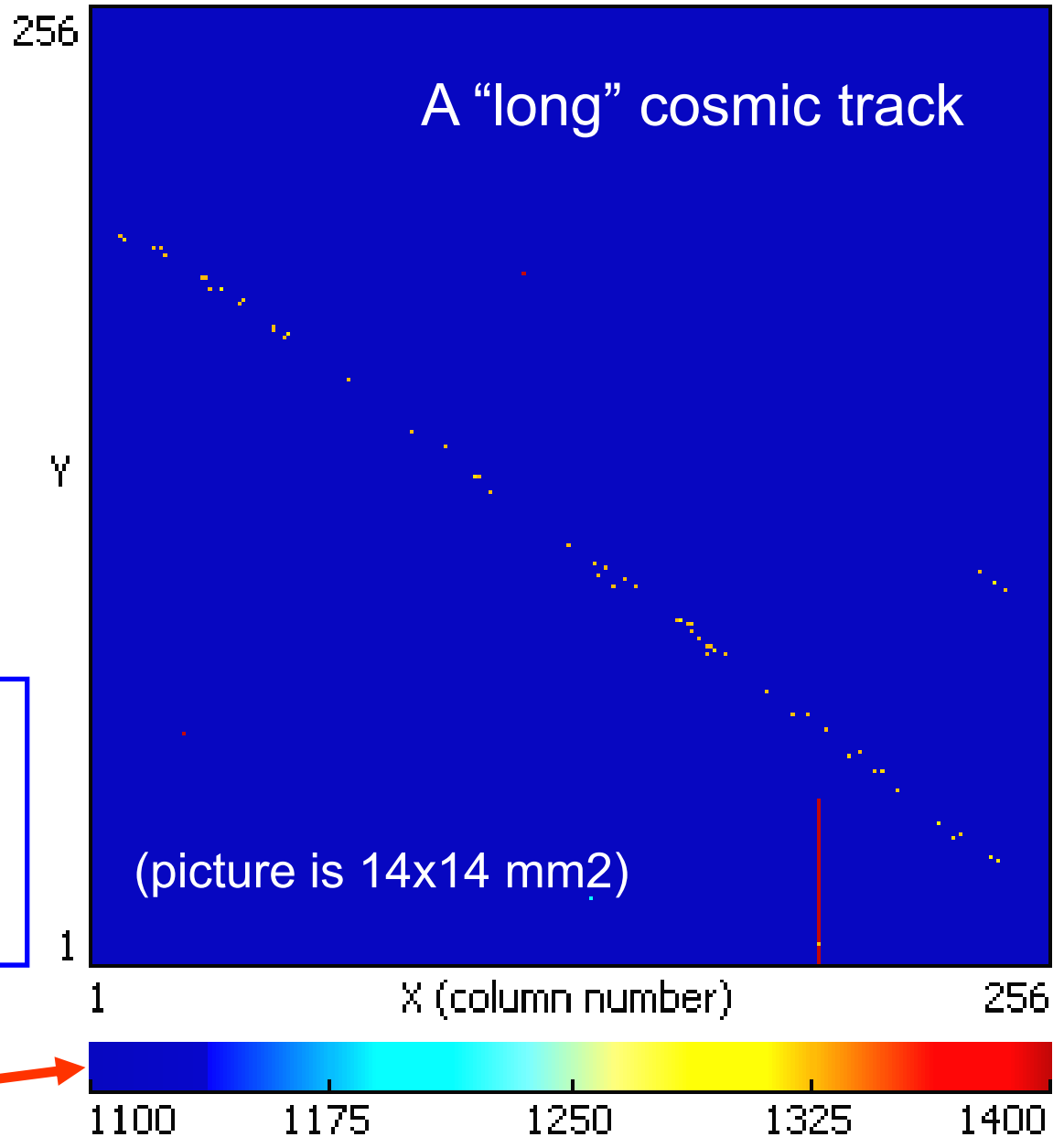
courtesy David Attié

The “typical” track

Timepix
+
20 μm thick
SiProt
+
Ingrid

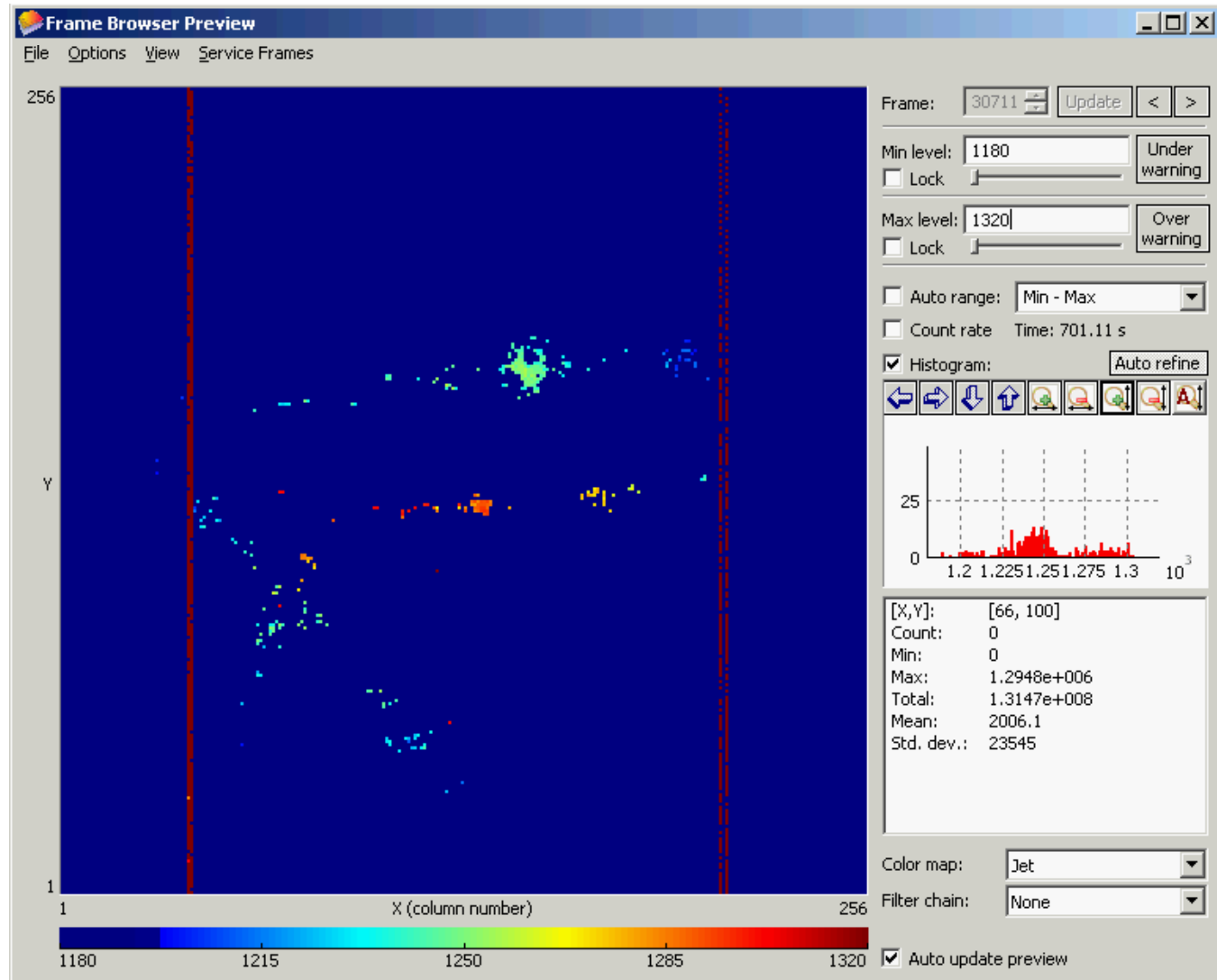
Stable operation in He
iC4H10

Will 20 μm SiProt be
enough to operate in Ar?



Stable operation in Argon too!

Time mode

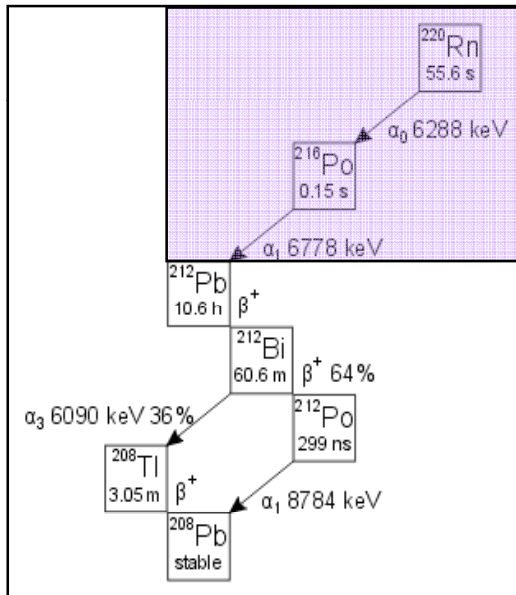


After 2 weeks of cosmic event recording, it was time for a definitive assessment whether 20 μm SiProt is enough to protect against discharges...

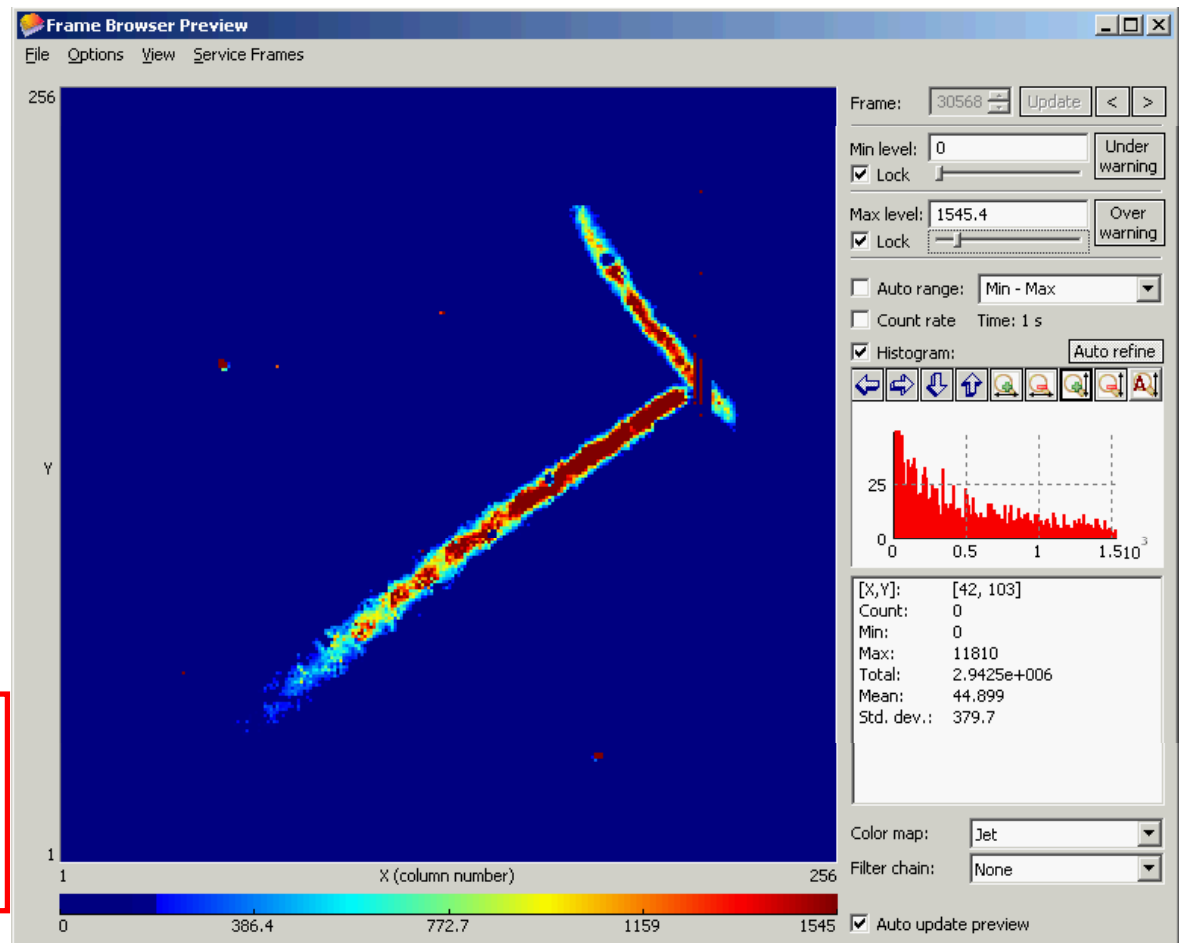
Final assessment: spark-proofness

- Provoke discharges by introducing small amount of Thorium in the Ar gas
 - Thorium decays to Radon 222 which emits **2 alphas of 6.3 & 6.8 MeV**
 - Depose on average $2.5 \cdot 10^5$ & $2.7 \cdot 10^5$ e- in Ar/iC₄H₁₀ 80/20 at -420 V on the grid, likely to trigger discharges

Charge mode



During ~3 days, some $5 \cdot 10^4$ alpha events recorded in 1% of which ...



... discharges are observed !

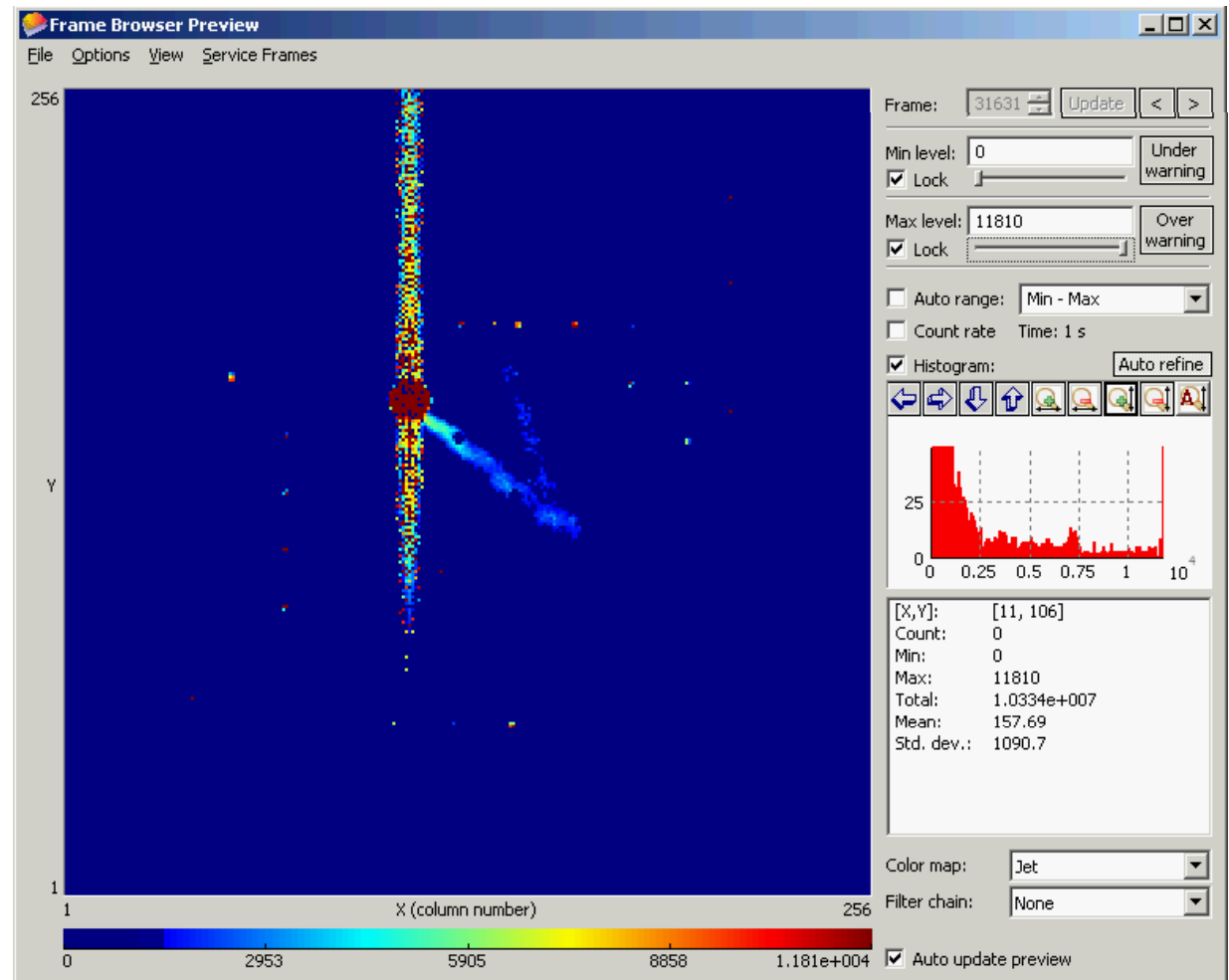
For the 1st time: image of discharges are being recorded

Round-shaped pattern of some 100 overflow pixels

Perturbations in the concerned column pixels

- Threshold?
- Power?

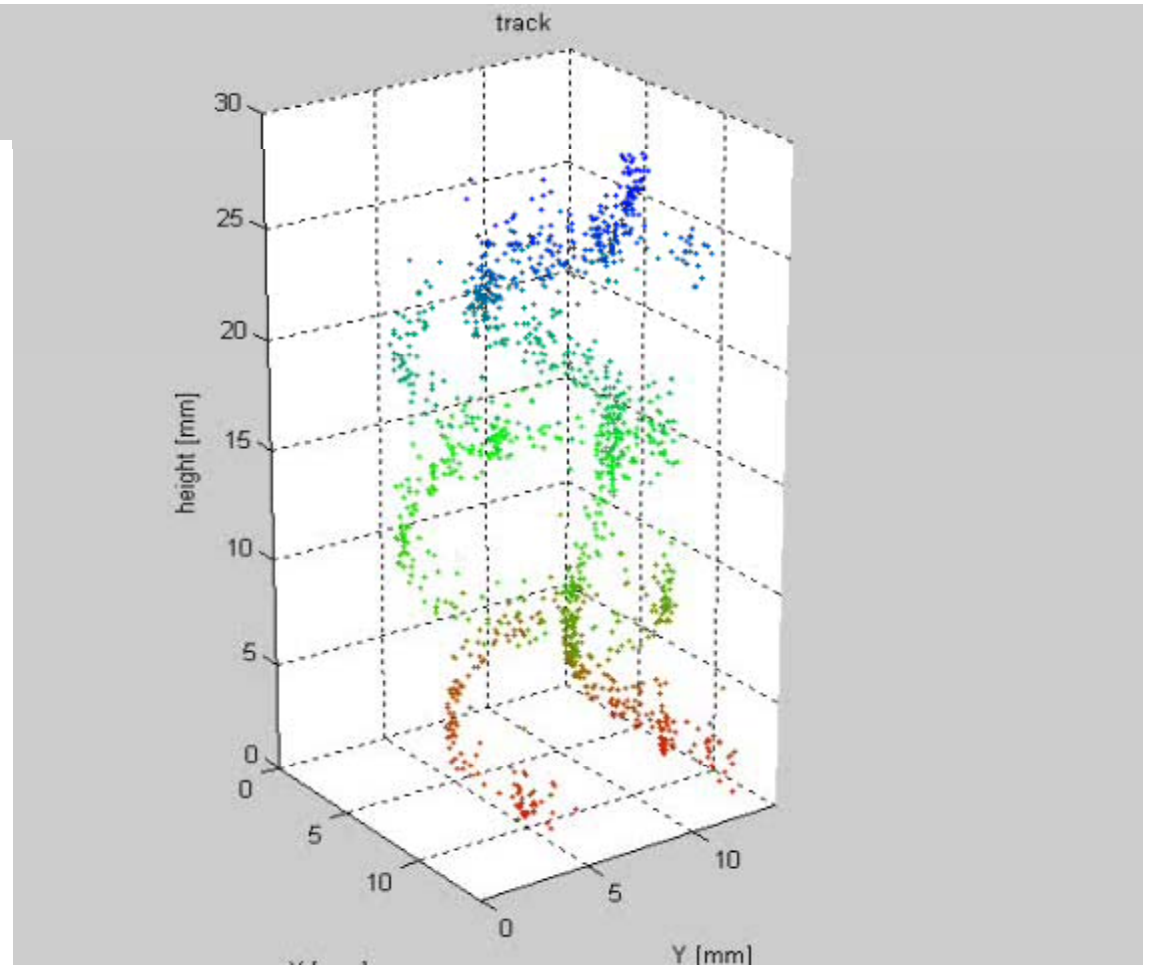
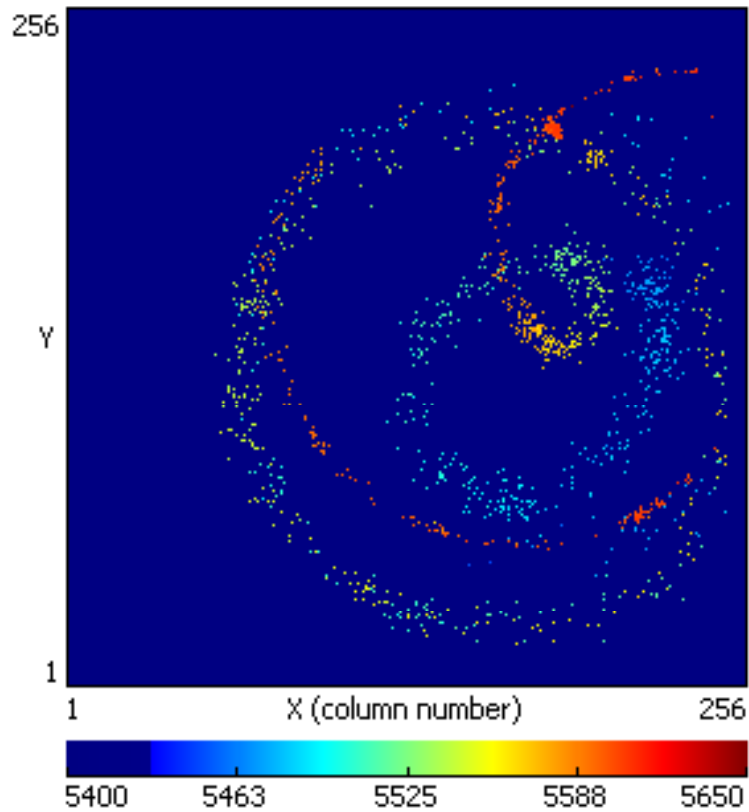
Chip keeps working !!



Sofar with 20 μm no more Timepix chip
damaged by discharges

A 5 cm³ TPC (two electron tracks from ⁹⁰Sr source)

$B = 0.2 \text{ T}$



Pixel systems sofar....

- Timepix (also Medipix2) with triple-GEMs (Freiburg, Bonn)
- Timepix (also Medipix2) with single Micromegas (NIKHEF, Saclay)

Now:

- Timepix + amorphous Si (highly resistive) + integrated grid (Ingrid) (NIKHEF), soon also Saclay
Will compare performance different thickness of protection layer: 0, 5, 10, 15 and 20 μm
- larger drift lengths, up to 100 mm

- **Sofar** single-chip systems used
- **Soon** (Eudet deliverable) small multi-chip systems:
 - Bonn: two 4-chip boards → on endplate module
 - Saclay: one 8-chip board → on endplate module
 - NIKHEF: 4-chip board, fitting single-chip detector mechanics and drifter (could become endplate module)
- **Later (~3/2009)**: aim for a 64-chip system (NIKHEF; may be too ambitious; bottleneck could be production of sufficient # Ingrids)

Summary

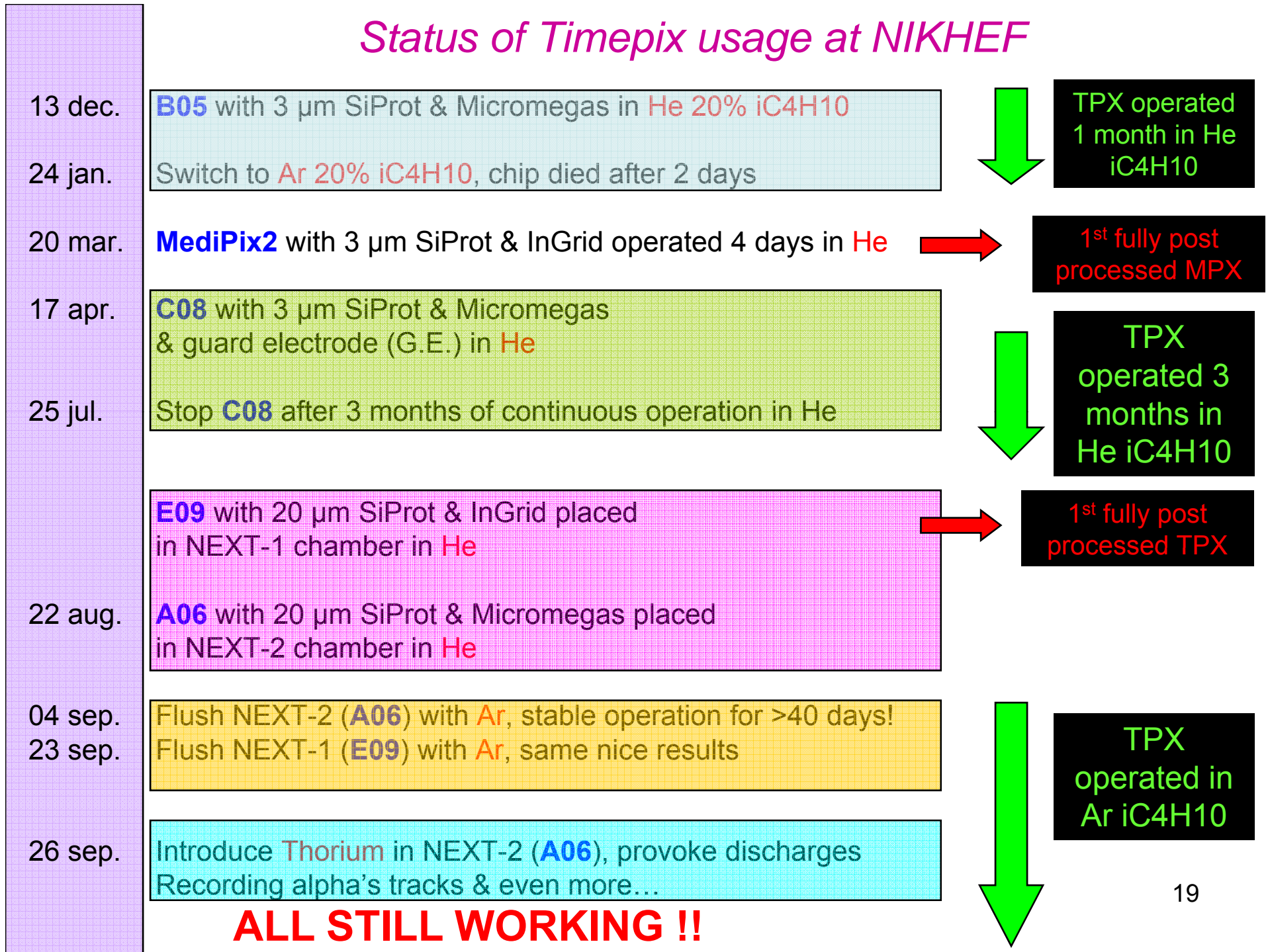
- A lot of progress made in last 'year'; not mentioned many details on track resolution studies and on signal development
- Part of the technology is ready:
 - Very good energy resolution for Ingrid devices
 - Ion backflow at the few per-mil level at high field ratio
- Discharge protection seems working for Ingrid (and Micromegas) devices
- Robust operation with GEM devices (without protection)

Next:

- Build larger multi-chip detector systems with fast readout

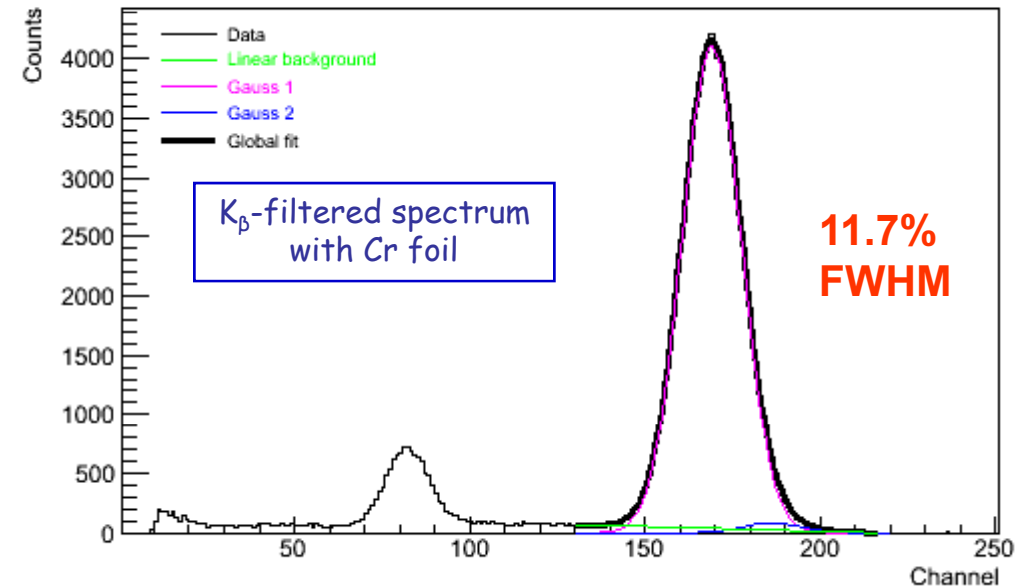
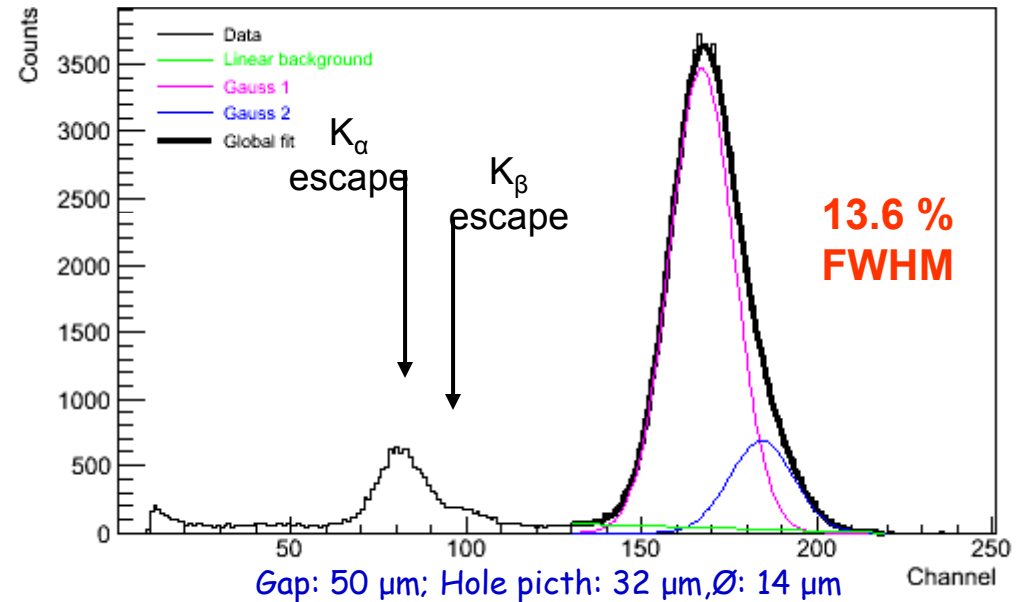
Backup slides

Status of Timepix usage at NIKHEF



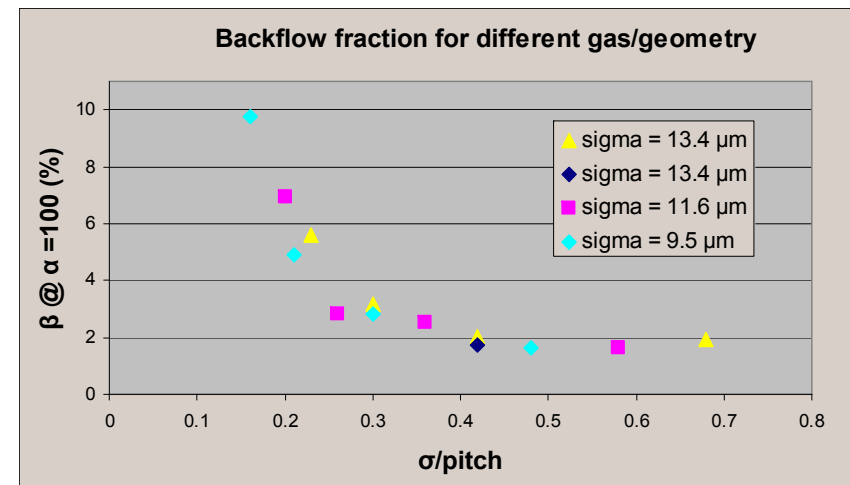
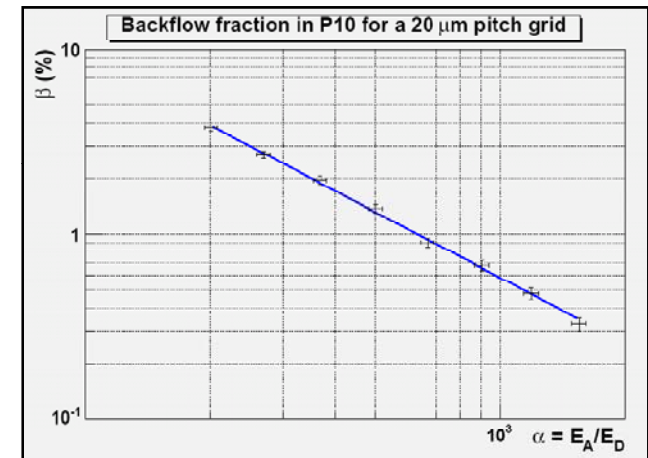
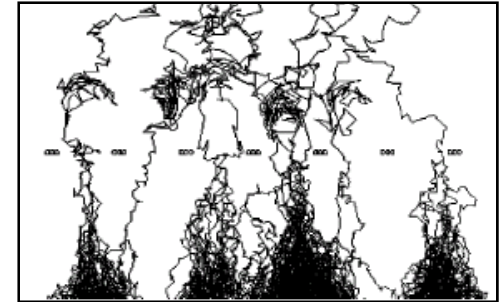
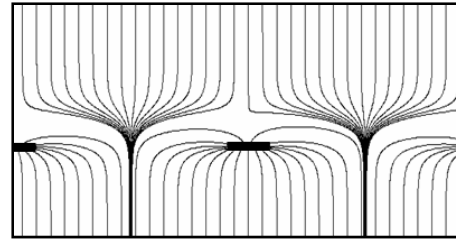
New Ingrid developments and results

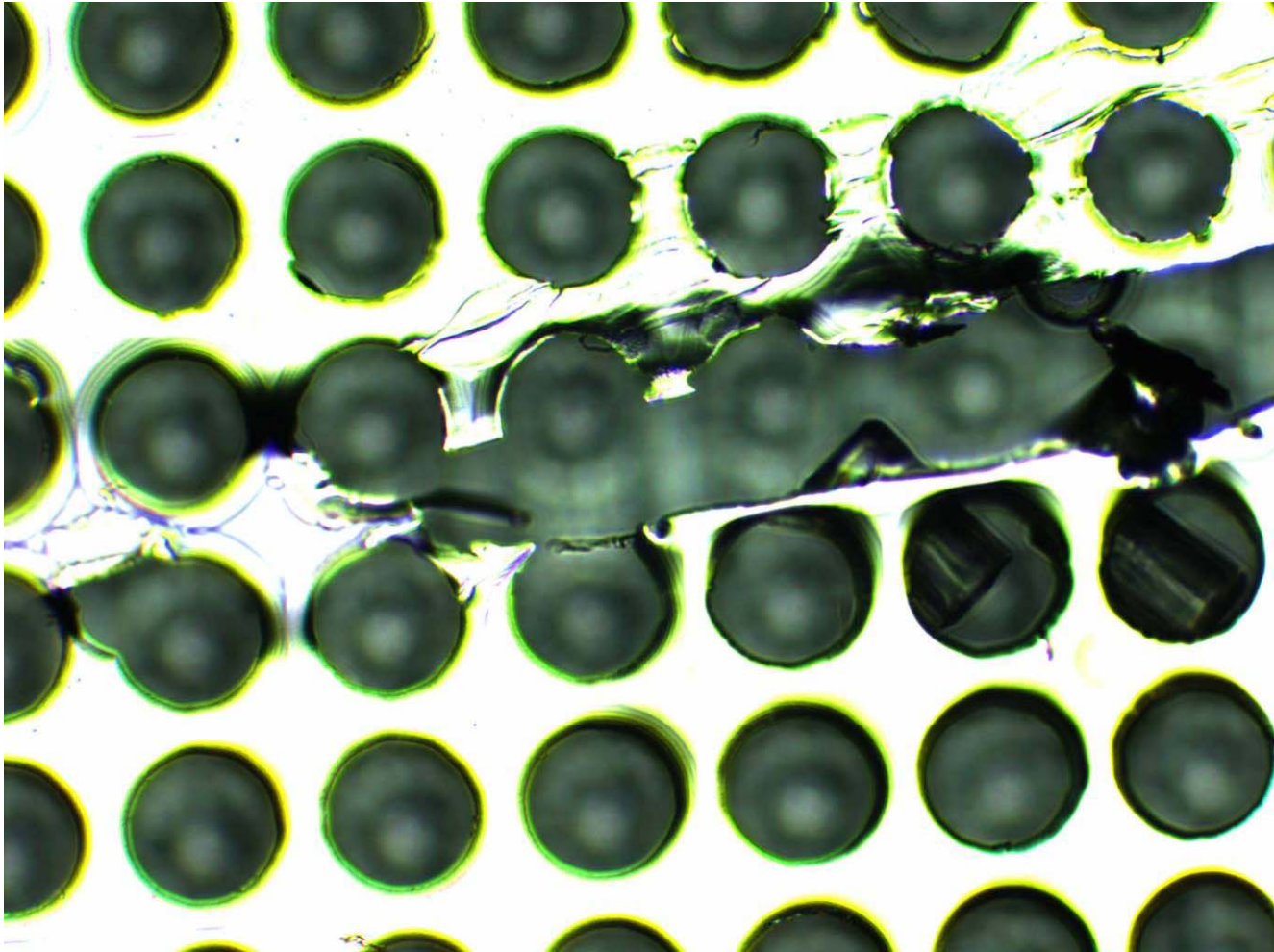
- Process improvement: grids much flatter
 - **Extremely good energy resolution:**
13.6 % FWHM with ^{55}Fe in P10
 - Removal of K_β 6.5 keV line:
11.7 % @ 5.9 keV in P10
- New wafer masks:
hole pitches down to 20 μm
with various diameters and gaps
 - Investigate Micromegas geometry
 - **Test of the ion backflow theory**
- Until now: 1 μm thin Al
but can now be increased to 5 μm by
electrolysis
Expect less damaged from sparks



InGrid ion backflow measurements

- Phenomenon depends on:
 - Avalanche charge distribution
 - Funnel size
- therefore on the gas and grid geometry
 - Q density in the funnel decreases with the avalanche transverse diffusion
 - Funnel size decreases with the field ratio and hole pitch
- Backflow fraction reaches a (minimum) plateau
 - Occurs when ions backflow through neighboring holes
 - Simulation predicts this to occur at $\sigma/p = 0.5$





A “scratch” occurred during production Ingrid;
Loose parts removed. Ingrid working!

Measurement of discharge “spectrum” (signal from Ingrid recorded on digital scope)

